



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Features

- Complementary NPN/PNP
- NPN Transistor
 - $BV_{CEO} > 60V$
 - $I_C = 1A$ high Continuous Collector Current
 - Low Saturation Voltage $V_{CE(sat)} < 220mV @ 1A$
- PNP Transistor
 - $BV_{CEO} > -60V$
 - $I_C = -1A$ high Continuous Collector Current
 - Low Saturation Voltage $V_{CE(sat)} < -340mV @ -1A$
- P_D up to 2.47W for power demanding applications
- $R_{\theta JA}$ efficient, 40% lower than SOT26
- Low profile 0.6mm high package for thin applications

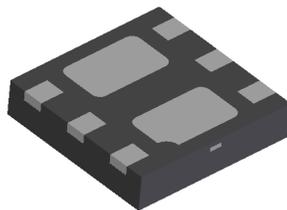
Mechanical Data

- Case: U-DFN2020-6
- UL Flammability Rating 94V-0
- Case Material: Molded Plastic. "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu, Solderable per MIL-STD-202, Method 208 ^(e4)
- Weight: 0.0065 grams (Approximate)

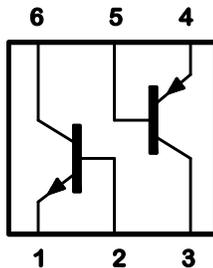
Application

- Gate Driving
- Load Switches
- Power Management
- Charging Circuits
- Power Switches (e.g. Motors, Fans)

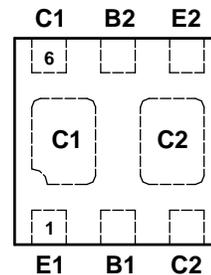
U-DFN2020-6



Bottom View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings – Q1 and Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	NPN	PNP	Unit
Collector-Base Voltage	V _{CB0}	60	-60	V
Collector-Emitter Voltage	V _{CEO}	60	-60	V
Emitter-Base Voltage	V _{EBO}	7	-7	V
Continuous Collector Current	I _C	1	-1	A
Peak Pulse Collector Current	I _{CM}	1.5	-1.5	A
Base Current	I _B	300	-300	mA
Peak Base Current	I _{BM}	1	-1	A

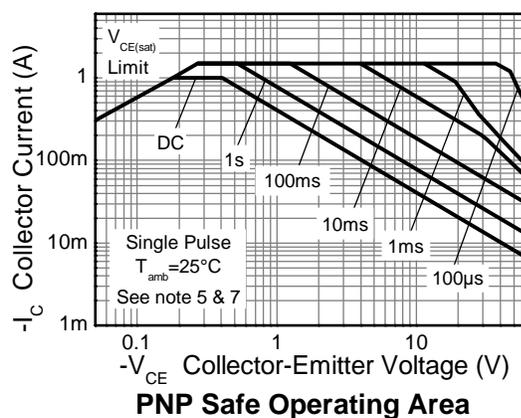
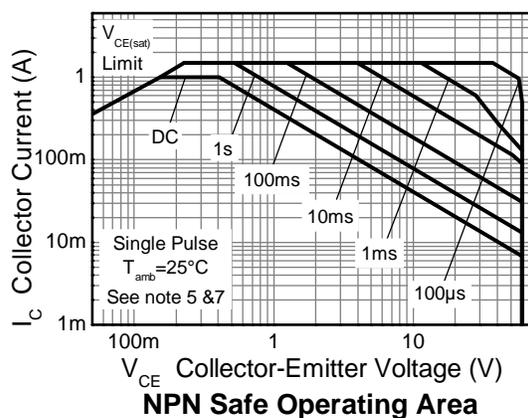
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	P _D	(Notes 5 & 7)	405	
		(Notes 5 & 8)	510	
		(Notes 6 & 7)	1650	
		(Notes 6 & 8)	2470	
Thermal Resistance, Junction to Ambient	R _{θJA}	(Notes 5 & 7)	308	
		(Notes 5 & 8)	245	
		(Notes 6 & 7)	76	
		(Notes 6 & 8)	51	
Thermal Resistance, Junction to Lead	(Note 9)	R _{θJL}	18	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

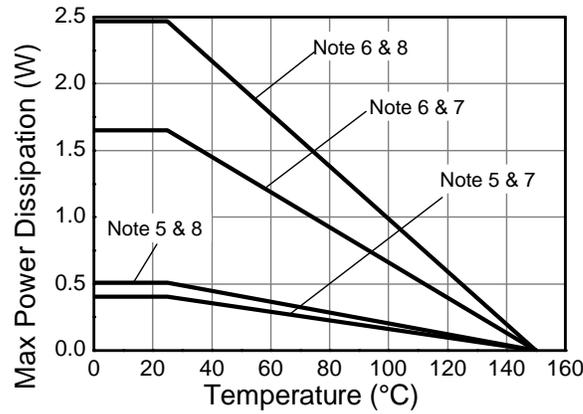
ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	C

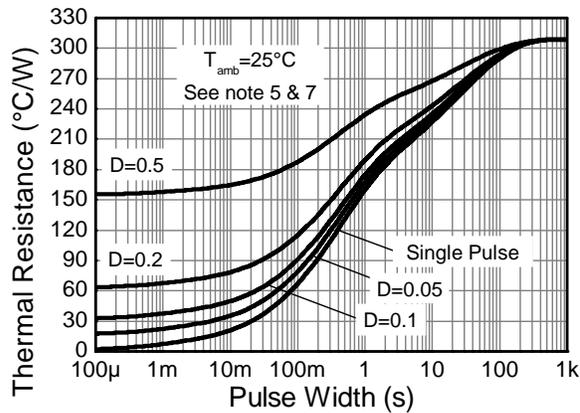
- Notes:
- For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as note (5), except the device is mounted with the collector pad on 28mm x 28mm (8cm²) 2oz copper.
 - For a dual device with one active die.
 - For dual device with 2 active die running at equal power.
 - Thermal resistance from junction to solder-point (on the exposed collector pads).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information


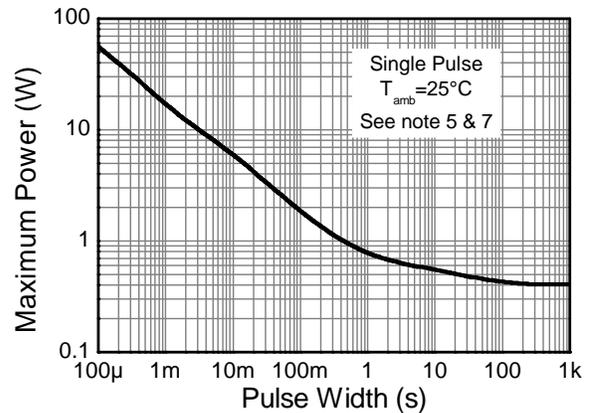
Thermal Characteristics and Derating Information



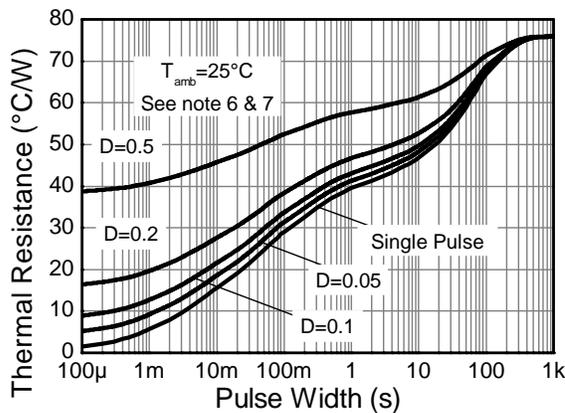
Derating Curve



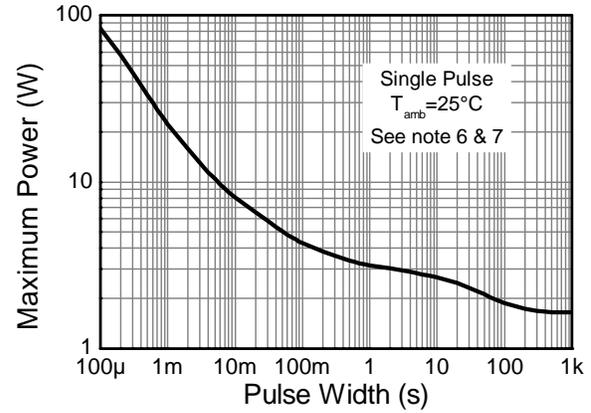
Transient Thermal Impedance



Pulse Power Dissipation



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics – Q1 NPN (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CB0}	60	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	60	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	—	—	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CB0}	—	—	100	nA	V _{CB} = 48V, I _E = 0
		—	—	50	μA	V _{CB} = 48V, I _E = 0, T _A = +150°C
Emitter-Base Cutoff Current	I _{EBO}	—	—	100	nA	V _{EB} = 5.6V, I _C = 0
DC Current Gain (Note 11)	h _{FE}	290	430	—	—	V _{CE} = 2V, I _C = 100mA
		150	220	—		V _{CE} = 2V, I _C = 500mA
		70	110	—		V _{CE} = 2V, I _C = 1A
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	—	90	120	mV	I _C = 500mA, I _B = 50mA
		—	170	220		I _C = 1A, I _B = 100mA
		—	185	240		I _C = 1A, I _B = 50mA
Equivalent On-Resistance (Note 11)	R _{CE(sat)}	—	180	240	mΩ	I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	—	—	1	V	I _C = 0.5A, I _B = 50mA
		—	—	1.1		I _C = 1A, I _B = 50mA
		—	—	1.1		I _C = 1A, I _B = 100mA
Base-Emitter Turn-on Voltage (Note 11)	V _{BE(on)}	—	—	0.9	V	V _{CE} = 2V, I _C = 0.5A
Transition Frequency	f _T	90	175	—	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz
Output (Collector) Capacitance	C _{ob(c)}	—	4	6	pF	V _{CB} = -10V, f = 1MHz
Turn-On Time	t _{on}	—	105	—	ns	V _{CC} = -10V, I _C = -0.5A, I _{B1} = -I _{B2} = 25mA
Delay Time	t _d	—	15	—	ns	
Rise Time	t _r	—	90	—	ns	
Turn-Off Time	t _{off}	—	540	—	ns	
Storage Time	t _s	—	410	—	ns	
Fall Time	t _f	—	130	—	ns	

Note: 11. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Electrical Characteristics – Q2 PNP (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CB0}	-60	—	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-60	—	—	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	—	—	V	I _E = -100μA
Collector-Base Cutoff Current	I _{CBO}	—	—	-100	nA	V _{CB} = -48V, I _E = 0
Emitter-Base Cutoff Current	I _{EBO}	—	—	-50	μA	V _{CB} = -48V, I _E = 0, T _A = +150°C
DC Current Gain (Note 11)	h _{FE}	—	—	-100	nA	V _{EB} = -5.6V, I _C = 0
DC Current Gain (Note 11)	h _{FE}	170	—	—	—	V _{CE} = -2V, I _C = -100mA
		120	—	—		V _{CE} = -2V, I _C = -500mA
		70	—	—		V _{CE} = -2V, I _C = -1A
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	—	—	-180	mV	I _C = -500mA, I _B = -50mA
		—	—	-340		I _C = -1A, I _B = -100mA
		—	—	-550		I _C = -1A, I _B = -50mA
Equivalent On-Resistance (Note 11)	R _{CE(sat)}	—	—	360	mΩ	I _C = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	—	—	-1	V	I _C = -0.5A, I _B = -50mA
		—	—	-1.0		I _C = -1A, I _B = -50mA
		—	—	-1.1		I _C = -1A, I _B = -100mA
Base-Emitter Turn-on Voltage (Note 11)	V _{BE(on)}	—	—	-0.9	V	V _{CE} = -2V, I _C = -0.5A
Transition Frequency	f _T	65	—	—	MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz
Output Capacitance	C _{ob}	—	—	15	pF	V _{CB} = -10V, f = 1MHz
Turn-On Time	t _{on}	—	75	—	ns	V _{CC} = -10V, I _C = -0.5A, I _{B1} = -I _{B2} = 25mA
Delay Time	t _d	—	35	—	ns	
Rise Time	t _r	—	40	—	ns	
Turn-Off Time	t _{off}	—	265	—	ns	
Storage Time	t _s	—	230	—	ns	
Fall Time	t _f	—	35	—	ns	

Note: 11. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics - Q1 NPN (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

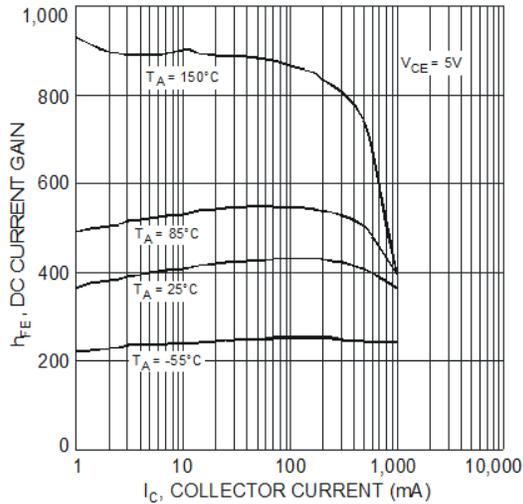


Fig. 1 Typical DC Current Gain vs. Collector Current

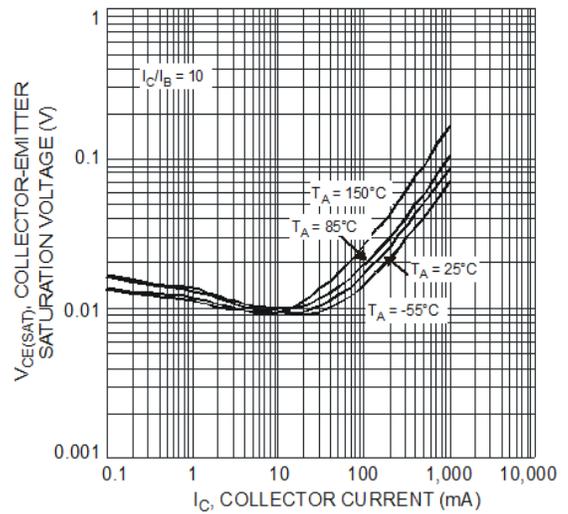


Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

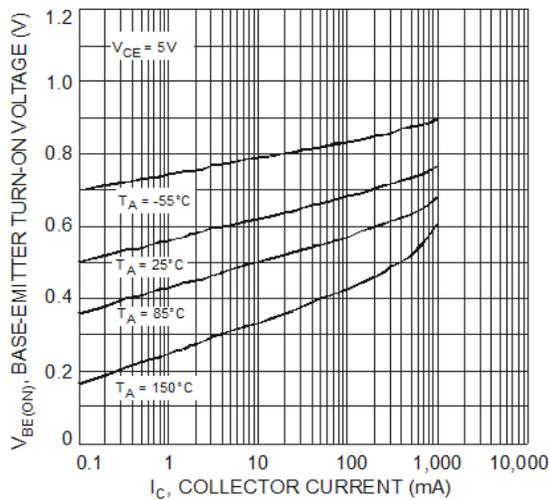


Fig. 3 Typical Base-Emitter Turn-On Voltage vs. Collector Current

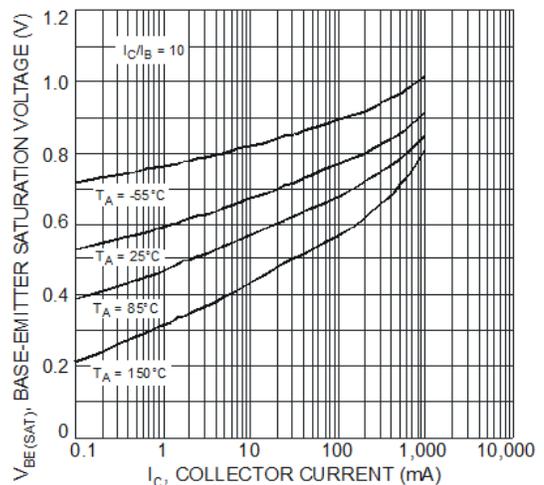


Fig. 4 Typical Base-Emitter Saturation Voltage vs. Collector Current

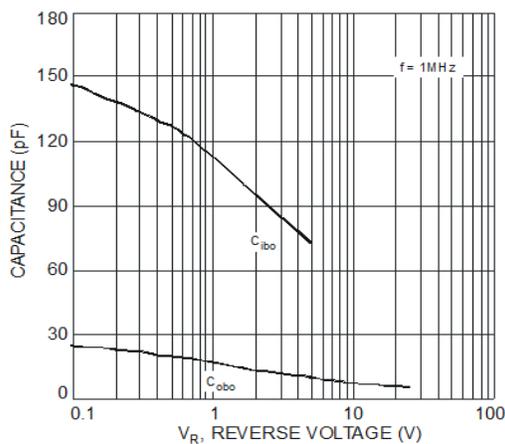
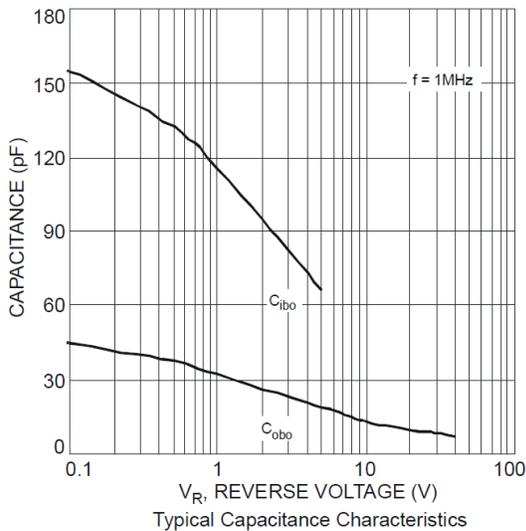
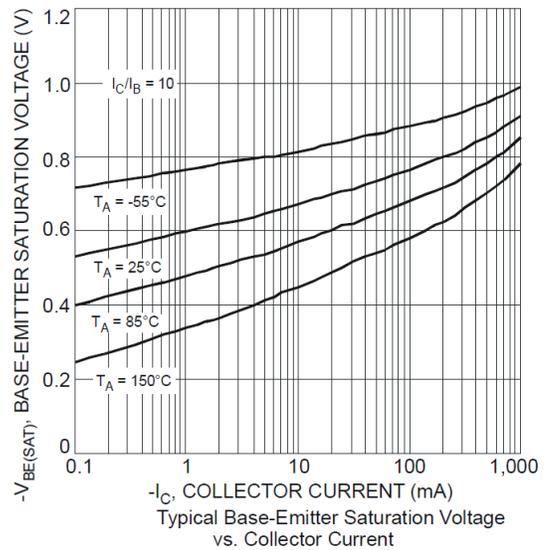
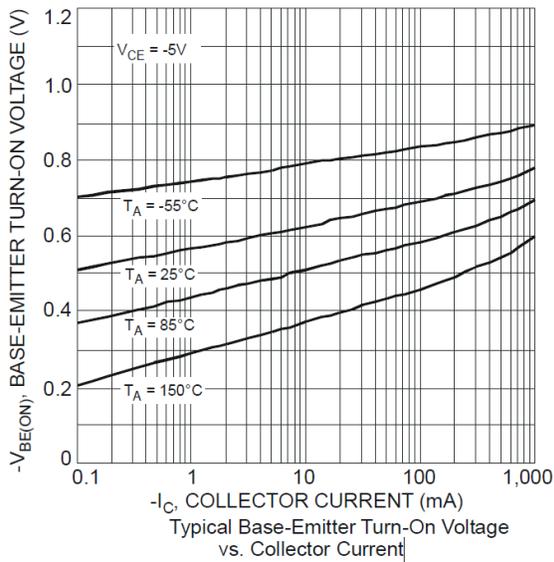
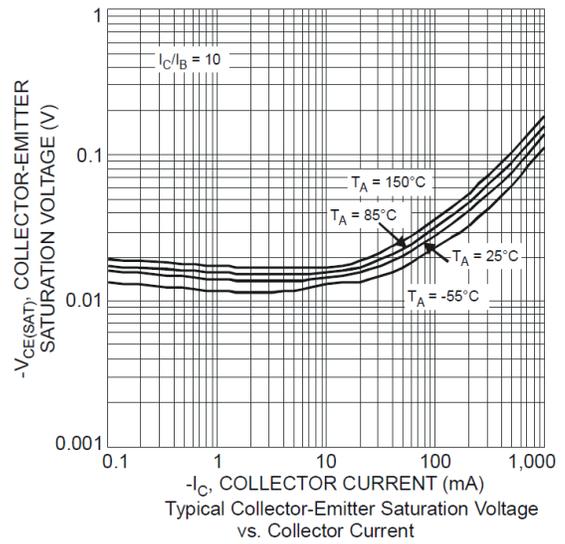
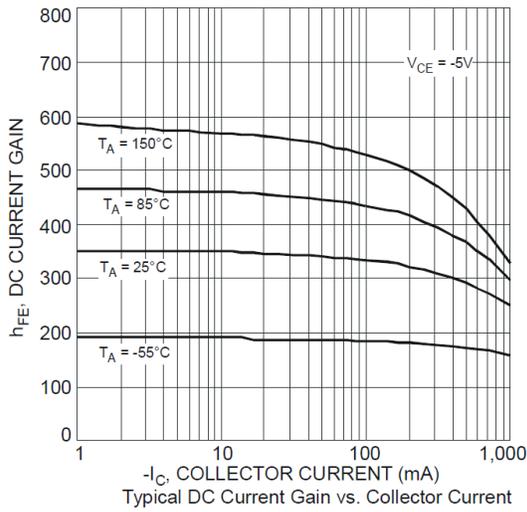
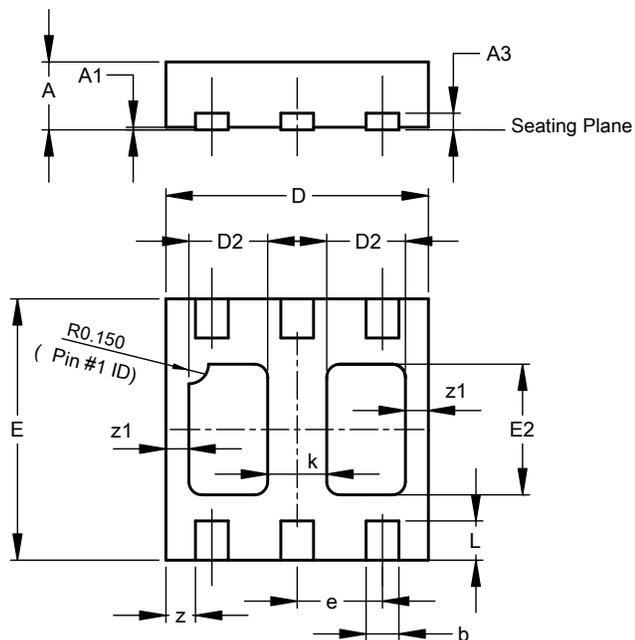


Fig. 5 Typical Capacitance Characteristics

Typical Electrical Characteristics - Q2 PNP (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

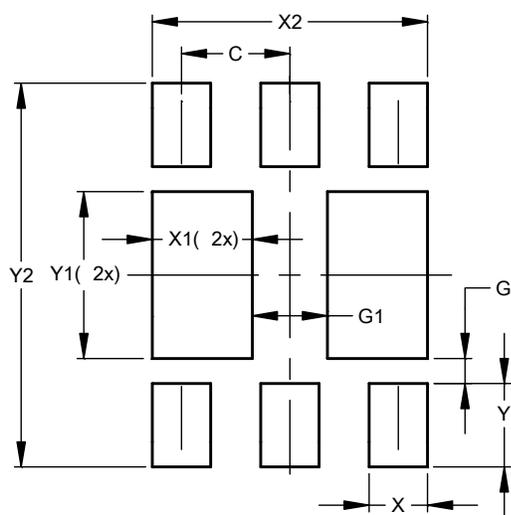


Package Outline Dimensions



U-DFN2020-6			
Type B			
Dim	Min	Max	Typ
A	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.175
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300